BATOP optoelectronics

SAM™ Data Sheet SAM-940-4-1ps-x, λ = 940 nm

Laser wavelength	λ = 940 nm
High reflection band	λ = 910 .. 990 nm
Absorbance	A_0 = 4 %
Modulation depth	ΔR = 2.6 %
Non-saturable loss	A_{ns} = 1.4 %
Saturation fluence	Φ_{sat} = 70 µJ/cm^2
Relaxation time constant	τ ~ 1 ps
Damage threshold	Φ = 3 mJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm
Protection	the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a copper heat sink with 12.7 mm ∅
x = 25.4 g	glued on a copper heat sink with 25.4 mm ∅
x = 12.7 s	soldered on a copper heat sink with 12.7 mm ∅
x = 25.4 s	soldered on a copper heat sink with 25.4 mm ∅
x = 25.0 h	soldered on a water cooled copper heat sink with 25.0 mm ∅
x = FC	mounted on a 1 m singlemode fiber cable with FC connector

low intensity spectral reflectance